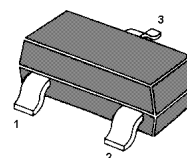


MMBTSA1037 PNP Silicon Epitaxial Planar Transistor

On special request, these transistors can be manufactured in different pin configurations.

FEATURES

- Excellent h_{FE} linearity.
- Compliments the 2SC2412



1.Base 2.Emmitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Current	$-I_C$	150	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

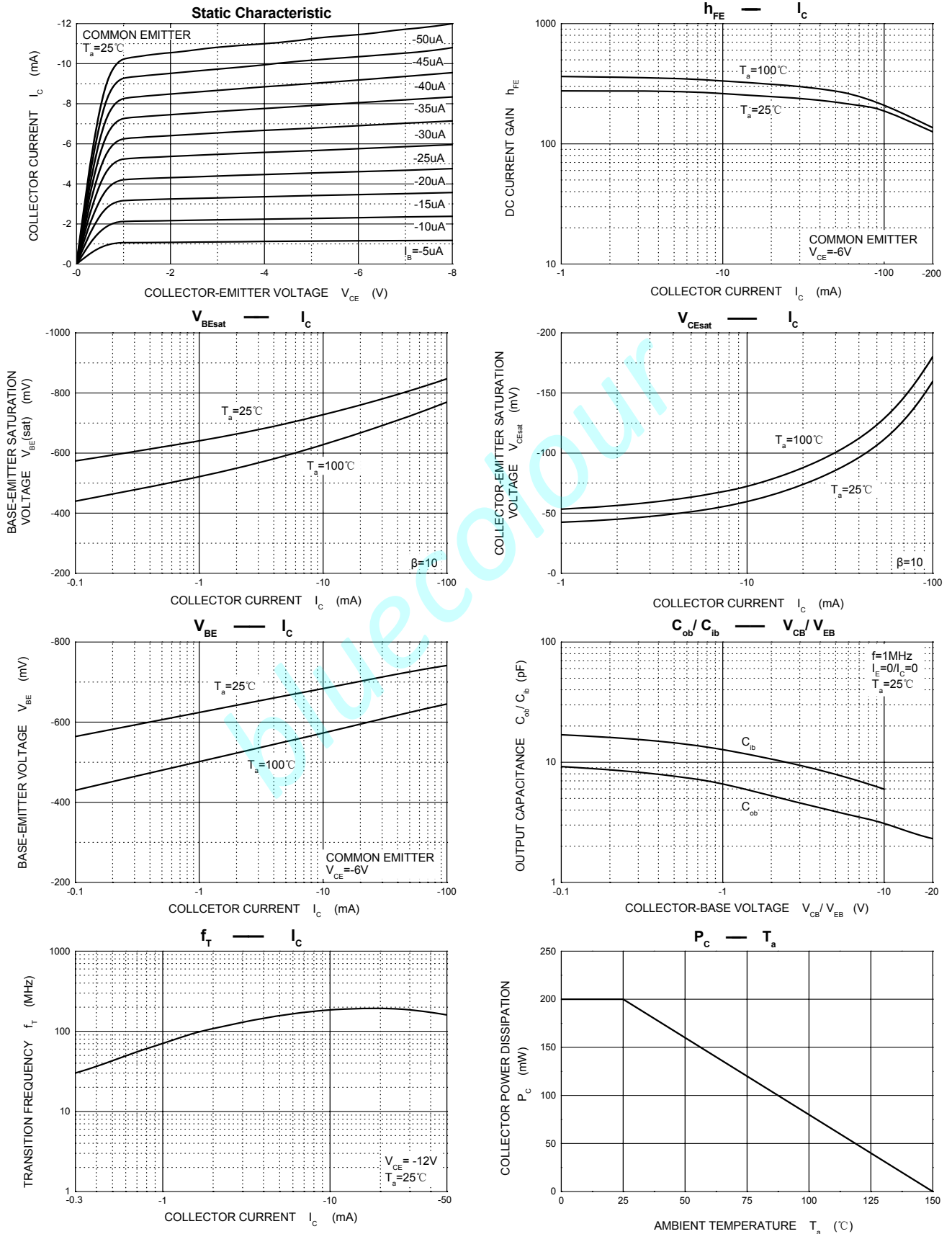
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6\text{V}, I_C = -1\text{mA}$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-0.5	V
Transition frequency	f_T	$V_{CE} = -12\text{V}, I_C = -2\text{mA}, f = 30\text{MHz}$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -12\text{V}, I_E = 0, f = 1\text{MHz}$		4.0	5.0	pF

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120 - 270	180 - 390	270 - 560
Marking	FQ	FR	FS

Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20